2SA673, 2SA673A

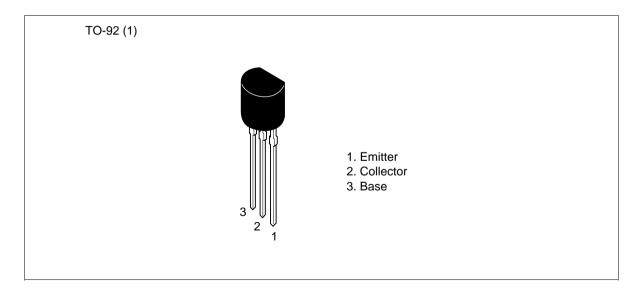
Silicon PNP Epitaxial

HITACHI

Application

- Low frequency amplifier
- Complementary pair with 2SC1213 and 2SC1213A

Outline





2SA673, 2SA673A

Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol	2SA673	2SA673A	Unit
Collector to base voltage	V_{CBO}	-35	-50	V
Collector to emitter voltage	V _{CEO}	-35	-50	V
Emitter to base voltage	V_{EBO}	-4	-4	V
Collector current	I _c	-500	-500	mA
Collector power dissipation	P _c	400	400	mW
Junction temperature	Tj	150	150	°C
Storage temperature	Tstg	-55 to +150	-55 to +150	°C

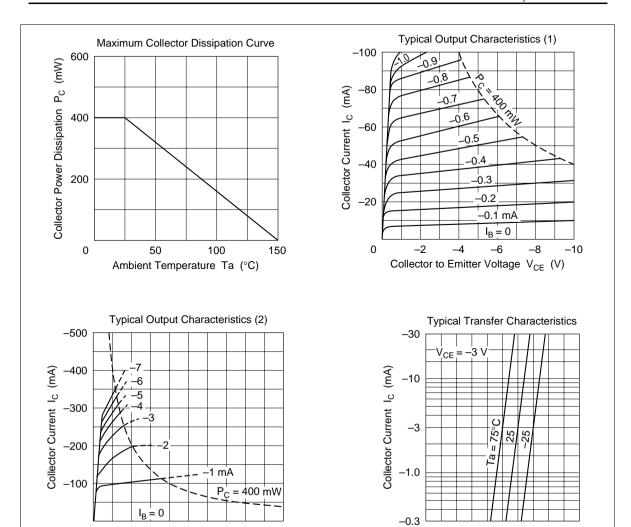
Electrical Characteristics (Ta = 25°C)

		2SA6	73		2SA673A				
Item	Symbol	Min	Тур	Max	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	-35	_	_	-50	_	_	V	$I_{c} = -10 \ \mu\text{A}, \ I_{E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-35	_	_	-50	_	_	V	$I_{\rm C} = -1$ mA, $R_{\rm BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-4	_	_	-4	_	_	V	$I_{E} = -10 \mu\text{A}, I_{C} = 0$
Collector cutoff current	I _{CBO}	_	_	-0.5	_	_	-0.5	μΑ	$V_{CB} = -20 \text{ V}, I_{E} = 0$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	-0.2	-0.6	_	-0.2	-0.6	V	$I_{\rm C} = -150 \text{ mA},$ $I_{\rm B} = -15 \text{ mA*}^2$
DC current trnsfer ratio	h _{FE} *1	60	_	320	60	_	320		$V_{CE} = -3 \text{ V},$ $I_{C} = -10 \text{ mA}$
DC current trnsfer ratio	h _{FE}	10	_	_	10	_	_		$V_{CE} = -3 \text{ V},$ $I_{C} = -500 \text{ mA}^{*2}$
Base to emitter voltage	V_{BE}	_	-0.64	_	_	-0.64	_	V	$V_{CE} = -3 \text{ V},$ $I_{C} = -10 \text{ mA}$

Notes: 1. The 2SA673 and 2SA673A are grouped by $h_{\rm FE}$ as follows.

2. Pulse test

В	С	D		
60 to 120	100 to 200	160 to 320		



0

-2

-4

-6

Collector to Emitter Voltage V_{CE} (V)

-8

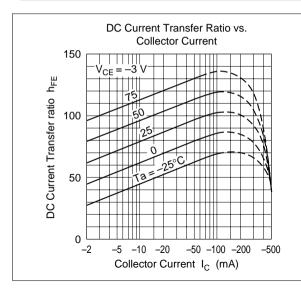
-10

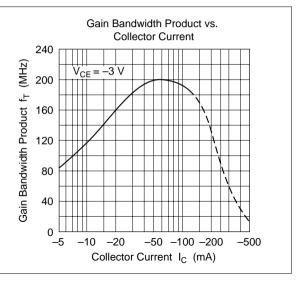
0

-0.2 -0.4 -0.6 -0.8 -1.0

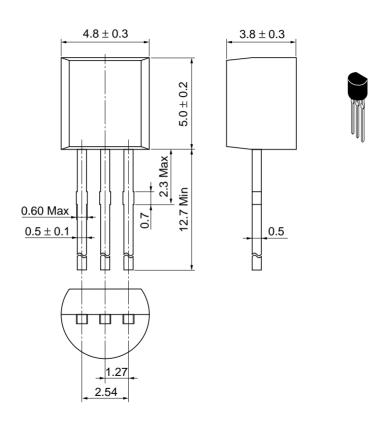
Base to Emitter Voltage V_{BE} (V)

2SA673, 2SA673A





Unit: mm



Hitachi Code	TO-92 (1)
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	0.25 g

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